

# New Jersey Semi-Conductor Products, Inc.

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2N4854, 2N4855

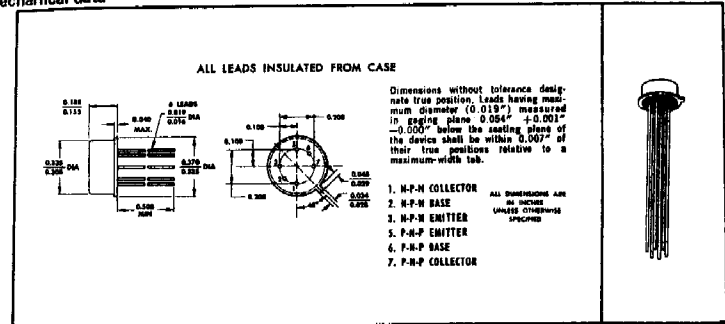
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## N-P-N, P-N-P DUAL SILICON TRANSISTORS

\*absolute maximum ratings at 25°C free-air temperature (unless otherwise noted) †

	EACH TRIODE DEVICE	TOTAL DEVICE
Collector-Base Voltage	60 V	
Collector-Emitter Voltage (See Note 1)	40 V	
Emitter-Base Voltage	5 V	
Collector-1-Collector-2 Voltage		±120 V
Lead-to-Case Voltage		±120 V
Continuous Collector Current	600 mA	
Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 2)	300 mW	600 mW
Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	1 W	2 W
Storage Temperature Range		-65°C to 200°C
Lead Temperature 1/16 Inch from Case for 10 Seconds		← 300°C →

\*mechanical data



NOTES: 1. This value applies between 0 and 600 mA collector current when the base-emitter diode is open-circuited. 40 V and 600 mA collector current may be simultaneously applied provided the time of application is 10  $\mu$ s or less and the duty cycle is 2% or less.  
2. Derate linearly to 175°C free-air temperature at the rates of 2 mW/°C for each triode and 4 mW/°C for total device.  
3. Derate linearly to 175°C case temperature at the rates of 6.67 mW/°C for each triode and 13.33 mW/°C for total device.  
† JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.  
† Voltages and currents apply to the N-P-N triode. For the P-N-P triode the values are the same, but the signs are reversed.

\*electrical characteristics at 25°C free-air temperature (unless otherwise noted) †  
individual triode characteristics (see note 4)

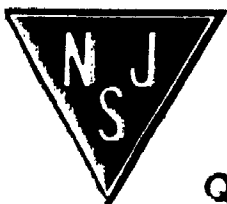
PARAMETER	TEST CONDITIONS	2N4854		2N4855		UNIT
		MIN	MAX	MIN	MAX	
V(BR)CBO Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	60		60		V
V(BR)CEO Collector-Emitter Breakdown Voltage	$I_C = 10 mA, I_B = 0$ , See Note 5	40		40		V
V(BR)EBO Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5		5		V
I <sub>CBO</sub> Collector Cutoff Current	$V_{CB} = 50 V, I_E = 0, T_A = 150^\circ C$		10		10	nA
I <sub>EBO</sub> Emitter Cutoff Current	$V_{EB} = 3 V, I_C = 0$		10		10	nA
h <sub>FE</sub> Static Forward Current Transfer Ratio	$V_{CE} = 1 V, I_C = 150 mA$ , See Note 5		50		20	
	$V_{CE} = 10 V, I_C = 100 \mu A$		35		20	
	$V_{CE} = 10 V, I_C = 1 mA$		50		25	
	$V_{CE} = 10 V, I_C = 10 mA$ , See Note 5		75		35	
	$V_{CE} = 10 V, I_C = 150 mA$ , See Note 5		100	300	40	120
	$V_{CE} = 10 V, I_C = 300 mA$ , See Note 5		35		20	
V <sub>BE</sub> Base-Emitter Voltage	$I_B = 15 mA, I_C = 150 mA$ , See Note 5	0.75	1.2	0.75	1.2	V
V <sub>CE(sat)</sub> Collector-Emitter Saturation Voltage	$I_B = 15 mA, I_C = 150 mA$ , See Note 5		0.4		0.4	V
h <sub>ie</sub> Small-Signal Common-Emitter Input Impedance		1.5	9	0.75	4.5	k $\Omega$
h <sub>fe</sub> Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 10 V, I_C = 1 mA, f = 1 kHz$		60	300	30	150
h <sub>oe</sub> Small-Signal Common-Emitter Output Admittance			50		25	$\mu$ mho
h <sub>fe</sub>   Small-Signal Common-Emitter Forward Current Transfer Ratio	$V_{CE} = 10 V, I_C = 20 mA, f = 100 MHz$		2		2	
C <sub>cb</sub> Collector-Base Capacitance	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$ , See Note 6		8		8	pF

\*operating characteristics at 25°C free-air temperature †  
individual triode characteristics (see note 4)

PARAMETER	TEST CONDITIONS	MAX	UNIT
t <sub>d</sub> Delay Time	$I_C = 150 mA, I_B(1) = 15 mA, V_{BE(off)} = -0.5 V$	20	ns
t <sub>r</sub> Rise Time	$R_L = 200 \Omega$ , See Note 7 and Figure 1	40	ns
t <sub>s</sub> Storage Time	$I_C = 150 mA, I_B(1) = 15 mA, I_B(2) = -15 mA$	280	ns
t <sub>f</sub> Fall Time	$R_L = 200 \Omega$ , See Note 7 and Figure 2	70	ns
F Spot Noise Figure	$V_{CE} = 10 V, I_C = 100 \mu A, R_G = 1 k\Omega, f = 1 kHz$	8	dB

NOTES: 4. The terminals of the triode not under test are open-circuited for the measurement of these characteristics.  
5. These parameters must be measured using pulse techniques.  $t_w = 300 \mu s$ , duty cycle < 2%.  
6. C<sub>cb</sub> measurement employs a three-terminal capacitance bridge incorporating a guard circuit. The emitter and case are connected to the guard terminal of the bridge.  
7. Voltages and current values shown are nominal; exact values vary with device parameters.

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